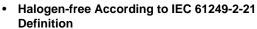
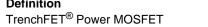
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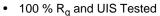
P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 40	0.012 at $V_{GS} = -10 \text{ V}$	- 60 ^d	60		
- 40	0.018 at $V_{GS} = -4.5 \text{ V}$	- 48 ^d	00		

FEATURES





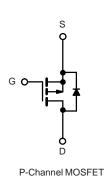


Compliant to RoHS Directive 2002/95/EC





D



APPLICATIONS · Power Switch

- Load Switch in High Current Applications
- DC/DC Converters

ABSOLUTE MAXIMUM RATINGS	T _C = 25 °C, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 40	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C		- 60 ^d	^	
Continuous Diain Current (1) = 150 C)	T _C = 70 °C	l _D	- 60 ^d		
Pulsed Drain Current		I _{DM}	- 180	A	
Avalanche Current		I _{AS}	- 46		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	106	mJ	
	T _C = 25 °C	В	73.5 ^b	W	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	P _D	2.5		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.7	C/VV		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS} $V_{DS} = 0 \text{ V, } I_{D} = -250 \mu\text{A}$		- 40				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 2.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		V _{DS} = - 40 V, V _{GS} = 0 V			- 1	μА	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 125 °C			- 50		
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 150 °C			- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 50			Α	
		V _{GS} = - 10 V, I _D = - 22 A		0.010	0.012		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 19 A		0.015	0.018	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 22 A		45		S	
Dynamic ^b				1	'		
Input Capacitance	C _{iss}			5380		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 20 V, f = 1 MHz		570			
Reverse Transfer Capacitance	C _{rss}	1		500			
Total Octo Observe G		V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 20 A		106	159	nC	
Total Gate Charge ^c				60	90		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$		22			
Gate-Drain Charge ^c	Q _{gd}]		27			
Gate Resistance	R _g	f = 1 MHz	0.4	1.8	3.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, R_{L} = 2 \Omega$		12	18		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω		70	105	ns -	
Fall Time ^c	t _f	1		18	27		
Drain-Source Body Diode Ratings a	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	I _S				- 60		
Pulsed Current	I _{SM}				- 180	A	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t _{rr}			35	53	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dI/dt = 100 A/μs		- 2	- 3	Α	
Reverse Recovery Charge	Q _{rr}			33	50	nC	

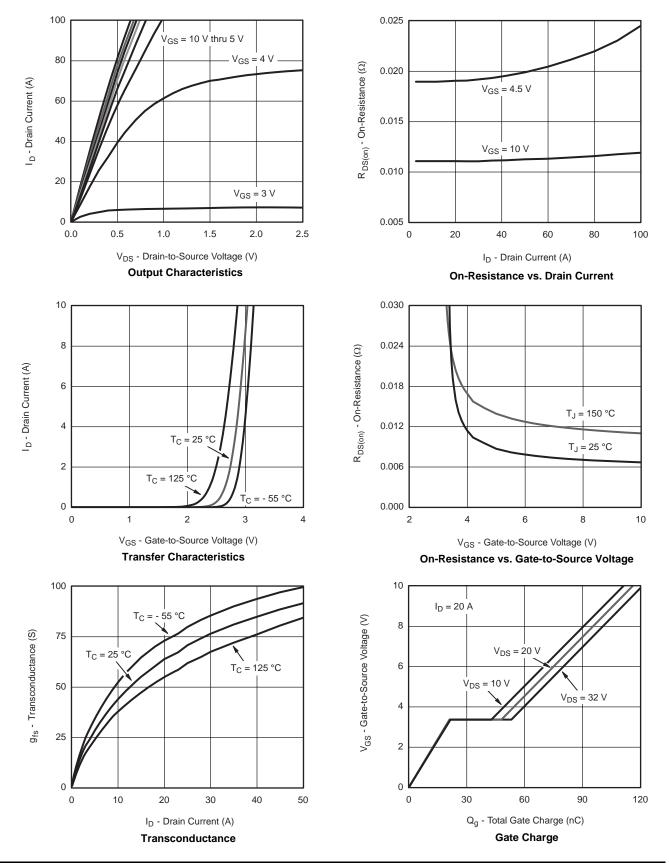
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

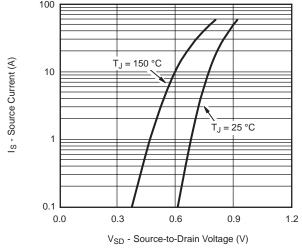


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

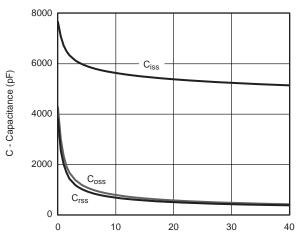




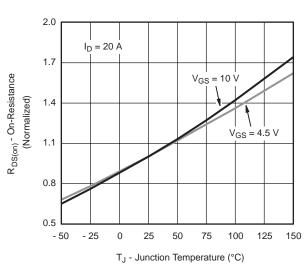
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



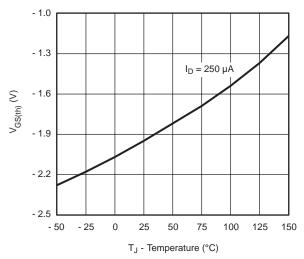
Source-Drain Diode Forward Voltage



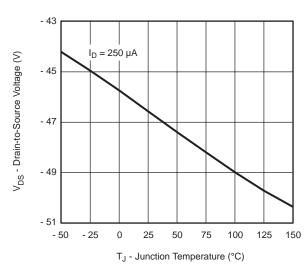
 V_{DS} - Drain-to-Source Voltage (V) ${f Capacitance}$



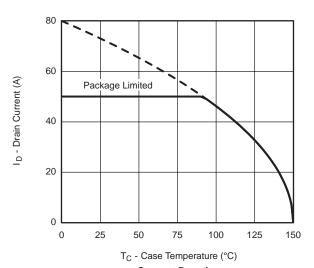
On-Resistance vs. Junction Temperature



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

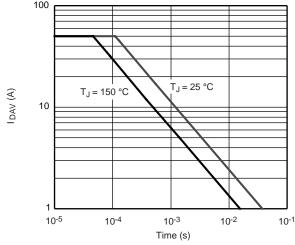


Current Derating

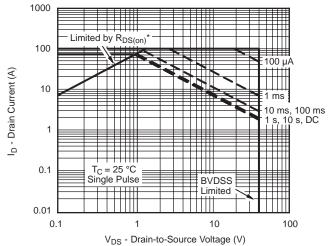
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

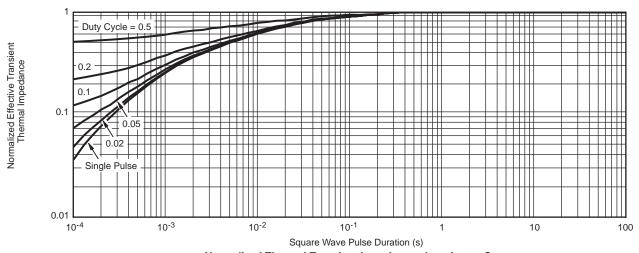


Single Pulse Avalanche Current Capability vs. Time



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

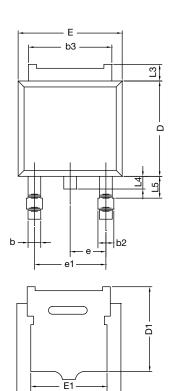


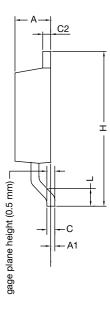
Normalized Thermal Transient Impedance, Junction-to-Case





TO-252AA CASE OUTLINE



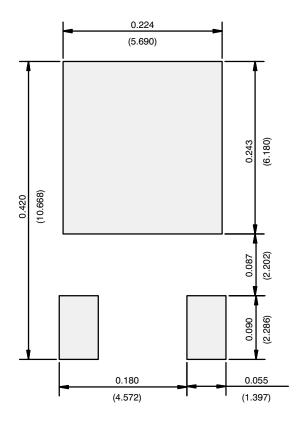


	MILLIMETERS IN			INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	4.56 BSC		BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

DWG: 5347 Note

• Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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